

---

# Early-Indicators for Failure-Prognosis of Electronics under Shock, Vibration and Thermo-mechanical Loads

*Task ID: NNA08BA21C*



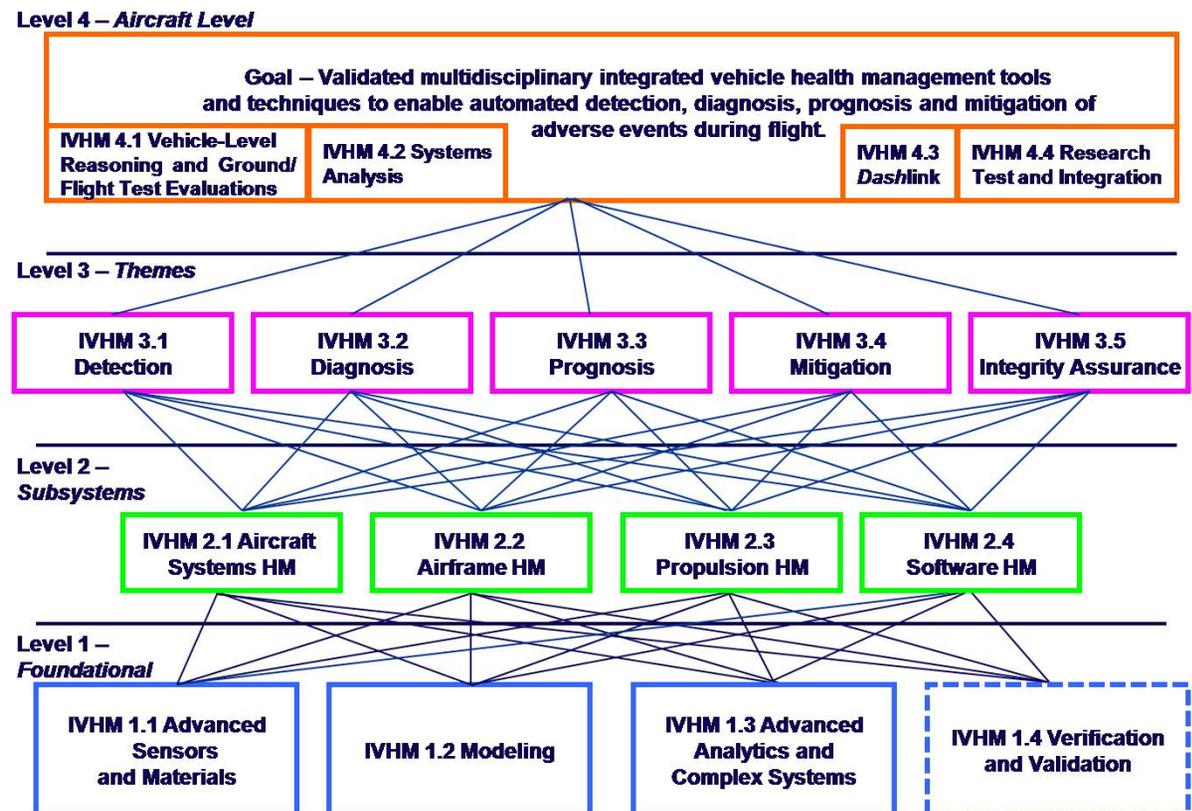
**INTEGRATED VEHICLE  
HEALTH MANAGEMENT**

**Pradeep Lall**

*Thomas Walter Professor and Center Director  
Auburn University  
Department of Mechanical Engineering  
NSF Center for Advanced Vehicle and Extreme  
Environment Electronics (CAVE<sup>3</sup>)  
Auburn, Auburn, AL 36849  
Tele: 334-844-3424  
E-mail: [lall@eng.auburn.edu](mailto:lall@eng.auburn.edu)*

# Outline

- Problem Statement
- Background
- IVHM milestones(s) being addressed
- Approach
- Results
- Conclusions
- Future Plans



# Problem Statement

---



Develop the Prognostic Health Management for electronics subjected to multiple cyclic thermo-mechanical loads, shock and vibration loads typical of deployed electronics.

Residual Life Assessment and decision support methods for re-deployment, operational readiness of systems based on accrued damage.

Develop the mathematical relationships correlating physical damage and feature-set for electronic systems in various harsh environment applications.

Statistical Assessment of response-repeatability for healthy components versus components with impending damage.

## ***Relationship to Adverse Events Table***

Slow Progression Fault: Very hard to detect, gradual degradation in performance

# Background

---

BIST gives ability to self-test and diagnose electronics with minimal interaction from external test equipment but limited insight into reliability [Chandramouli96, Drees04, Hassan92, Williams83, Zorian94]

Fuses and Canaries used for detecting and controlling faults in electronic system and restoring normal operating conditions are reactive diagnostic tools. [Anderson04, Mishra02 ].

Life-prediction models assume pristine systems, require acquisition and storage of environmental data, limited ability to predict life in complex environments.

Damage pre-cursors based on micro-structural evolution, time and spectral techniques for health monitoring of electronics. [Lall04<sup>a-d</sup>, 05<sup>a-b</sup>, 06<sup>a-f</sup>, 07<sup>a-e</sup>, 08<sup>a-f</sup> ].

# IVHM Milestones Addressed



## *IVHM 2.1: Aircraft Systems Health Management*

Development of methods that will enable detection, diagnostics, prognostics, and mitigation strategies for systems, including but not limited to electromechanical systems, avionics, electrical power systems, and electronics.

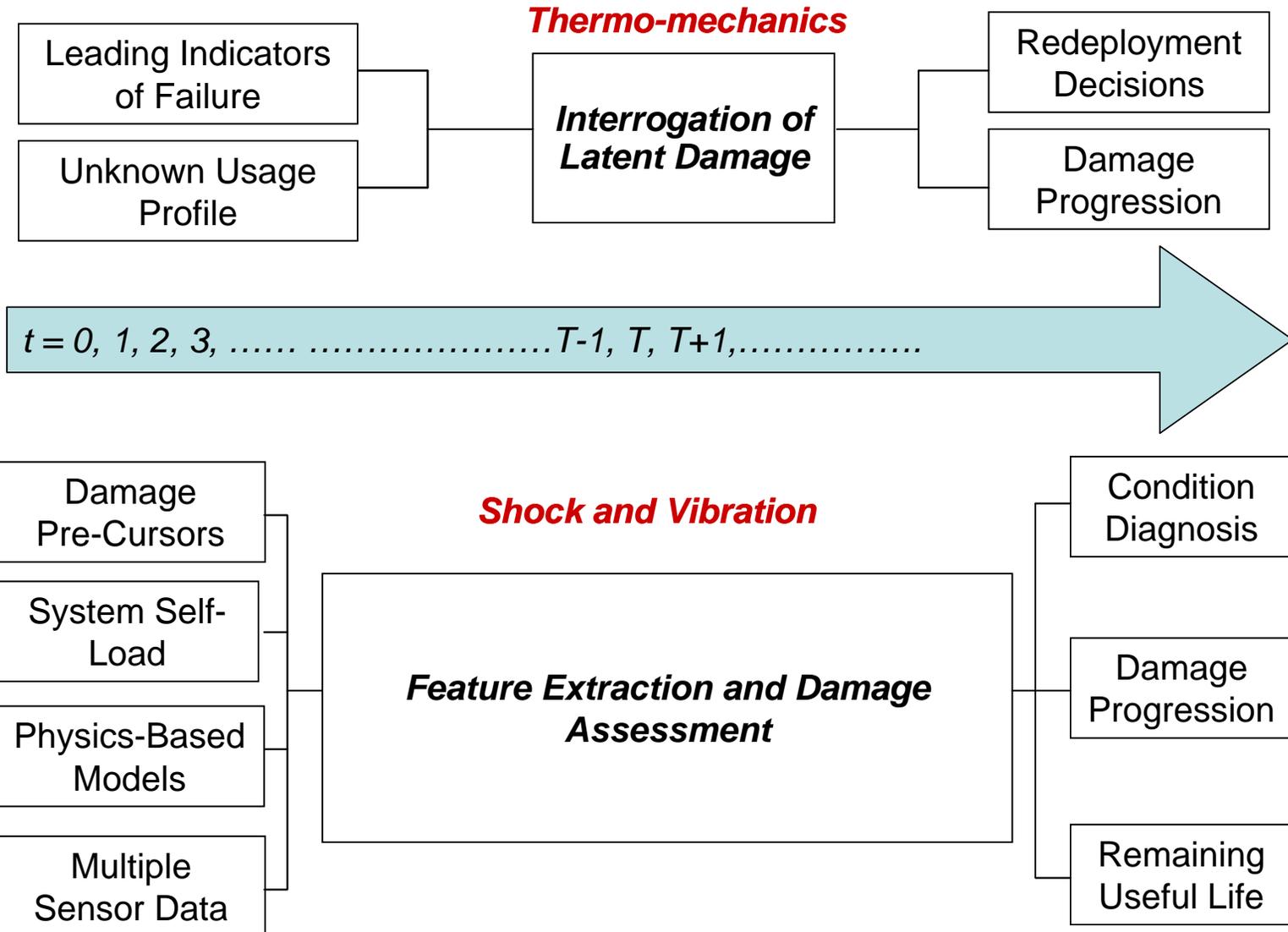
### *Relationship to IVHM Goal:*

Current program focuses on development of early indicators of damage for prognostication of electronics

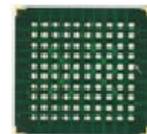
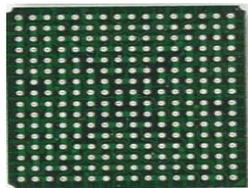
*Program Duration: 3-Years*

*Current Location in Time-Line: Near-end of Year-2*

# Approach: **cave**<sup>3</sup> PHM Framework



# Test Vehicle-A



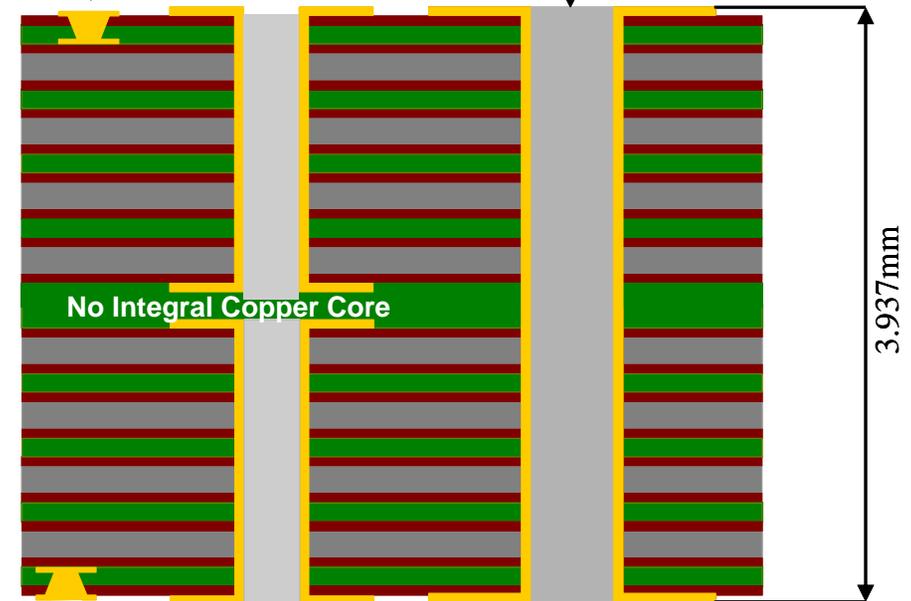
256 PBGA

100 CABGA

Solder	Sn3Ag0.5Cu	Sn3Ag0.5Cu
Package Size (mm)	17 x 17	12 x 12
Package Type	PBGA	CABGA
I/O Count	256	100
I/O Pitch (mm)	1	0.8
Ball Diameter (mm)	0.5	0.5
Die Size (mm)	7.94	5.58
P/D ratio	2.14	2.15
Board Finish	ENIG	ENIG
Substrate Pad Type	NSMD	NSMD

Microvia: Copper Filled, 0.004"

Through-hole



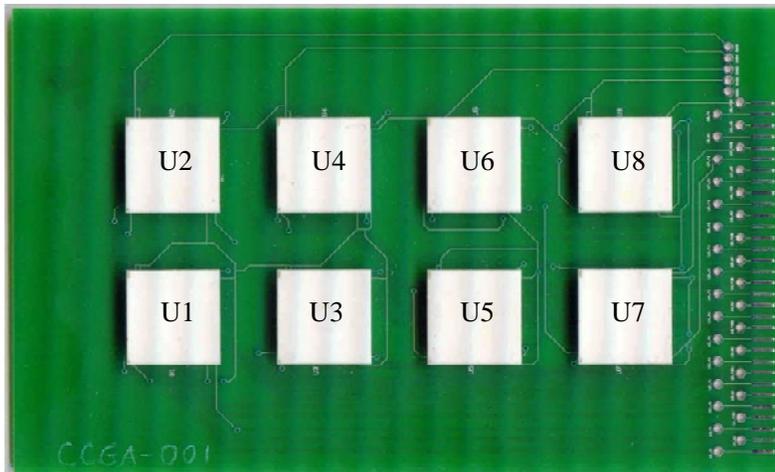
*Board Assembly, No-Core*

The assemblies have been subjected to relatively harsh thermal cycle (TC-1) temperature ranging from -55°C to 125°C, 2.5 hours/cycle followed by a milder thermal cycle (TC-2) temperature from 0°C to 100°C, 16 minutes Dwell and 8 minutes ramp.

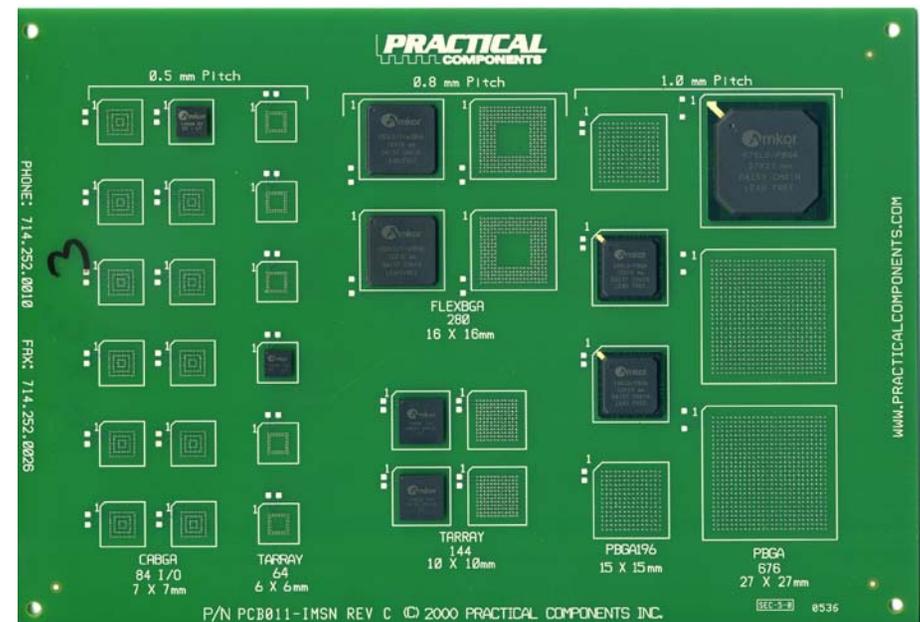
# Test Vehicle-B and C

Parameter	CCGA Cu-Columns	CBGA SnPb	CBGA Hi-Pb	CBGA SAC305
Solder	Sn15/Pb85	Sn63/Pb37	Sn10/Pb90	SAC305
Length	21 mm	21 mm	21 mm	21 mm
Width	21 mm	21 mm	21 mm	21 mm
Thickness	2.4 mm	2.4 mm	2.4 mm	2.4 mm
I/O	400	400	400	400
Pitch	1 mm	1 mm	1 mm	1 mm
Ball Dia	0.6 mm	0.6 mm	0.6 mm	0.6 mm
Jt Height	2 mm	0.6 mm	0.6 mm	0.6 mm

	6 mm Tape Array	7 mm Chip Array	10 mm Tape array	15 mm PBGA	16 mm Flex BGA	27 mm PBGA
I/O	64	84	144	196	280	676
Pitch (mm)	0.5	0.5	0.8	1	0.8	1
Die Size (mm)	4	5.4	7	6.35	10	6.35
Substrate Thick (mm)	0.36	0.36	0.36	0.36	0.36	0.36
Pad Dia. (mm)	0.28	0.28	0.30	0.38	0.30	0.38
Substrate Pad	NSMD	NSMD	NSMD	SMD	NSMD	SMD
Ball Dia. (mm)	0.32	0.48	0.48	0.5	0.48	0.63

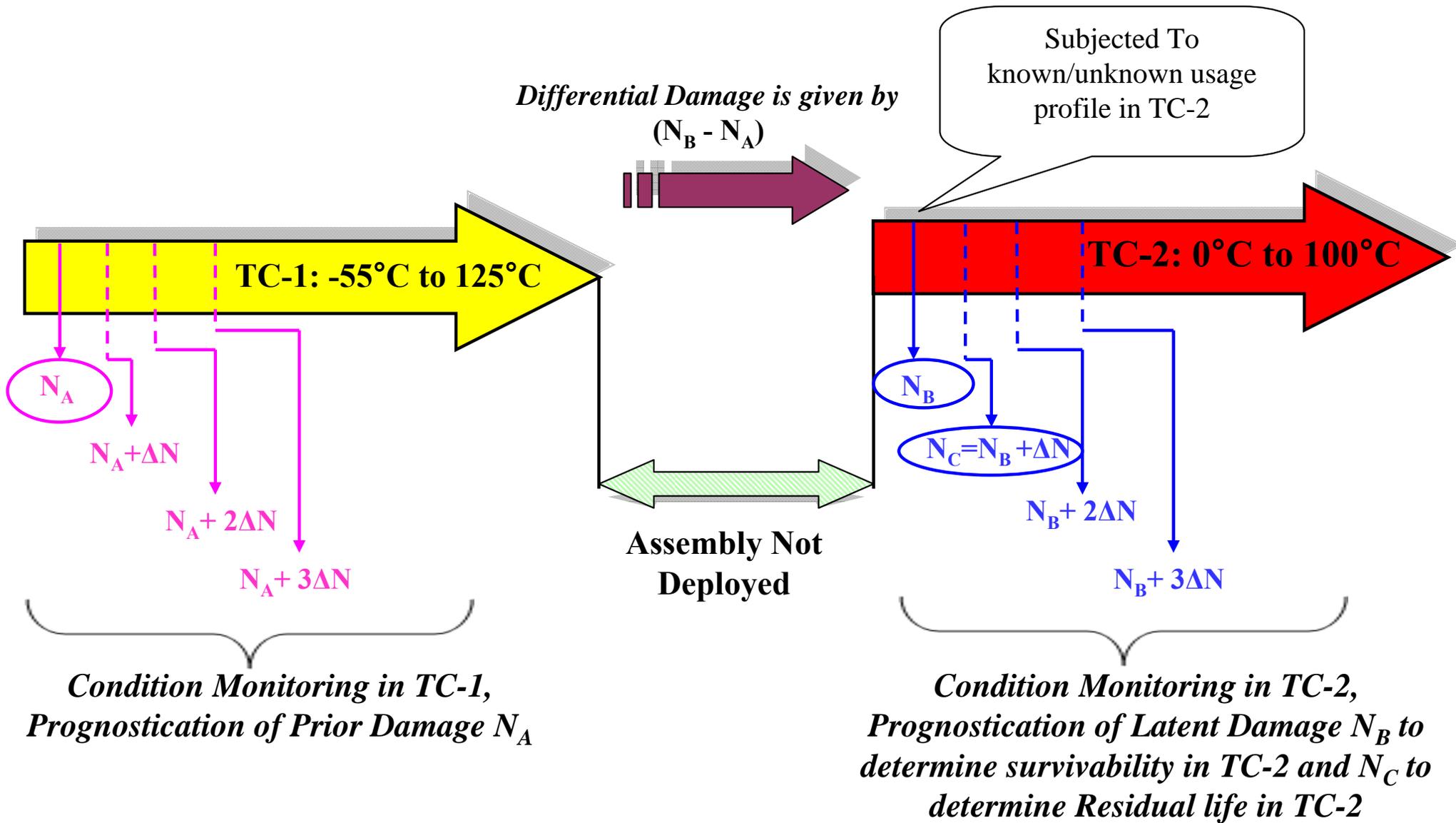


*Test Vehicle-B*



*Test Vehicle-C*

# Multiple Thermal-Environments



# Multiple Thermal-Environments

*Previously, it has been shown that.....*

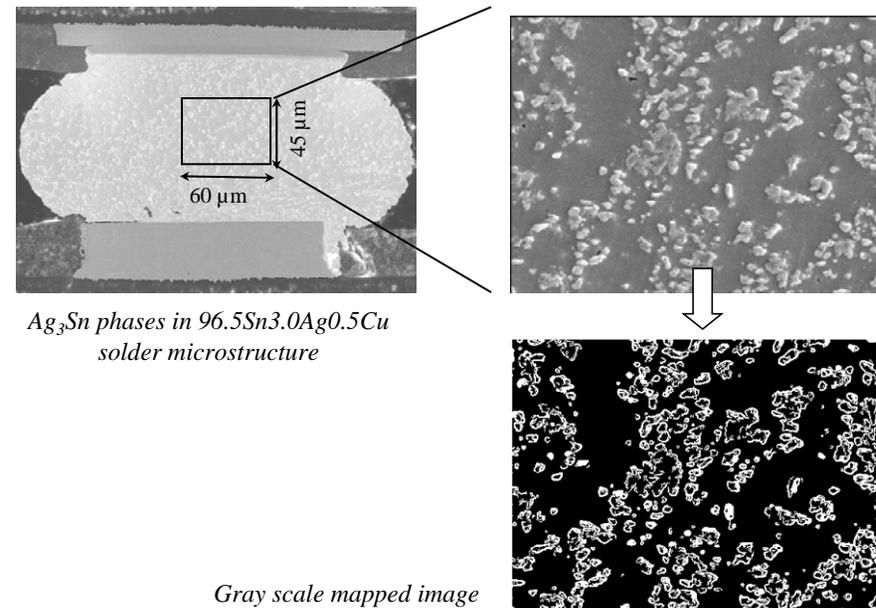
Rate of change in phase growth parameter  $[d(\ln S)/d(\ln N)]$  is valid damage proxy for prognostication of thermo-mechanical damage in solder interconnects and assessment of residual life [Lall 2004<sup>a</sup>, 2005<sup>a</sup>, 2006<sup>c,d</sup>, 2007<sup>c,e</sup>, 2008<sup>c,d</sup>].

Damage proxy  $[d(\ln S)/d(\ln N)]$  is related to the microstructural evolution of damage by the following equation:

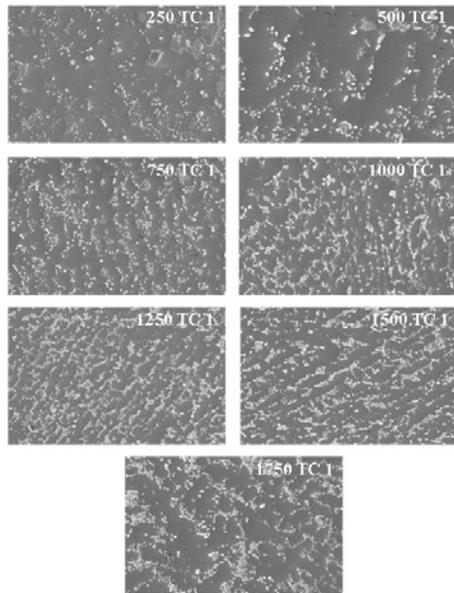
$$S = g^4 - g_0^4 = a(N)^b$$

$$\ln S = \ln(g^4 - g_0^4) = \ln a + b \ln N$$

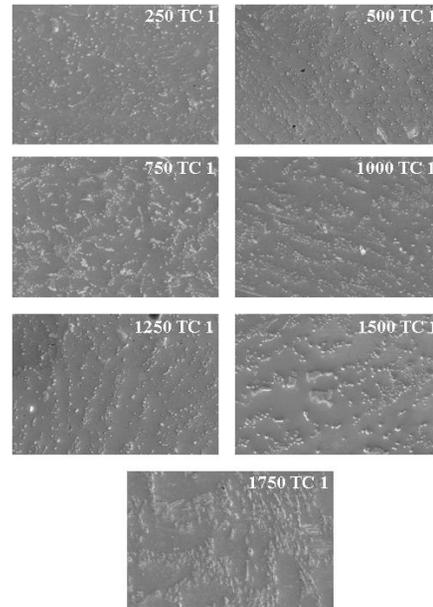
$$\frac{d(\ln S)}{d(\ln N)} = b$$



# Effect of $\Delta T$ Magnitude



*SEM backscattered images, -55°C to 125°C, 96.5Sn3.0Ag0.5Cu solder, 100 I/O CABGA, magnification 750x*

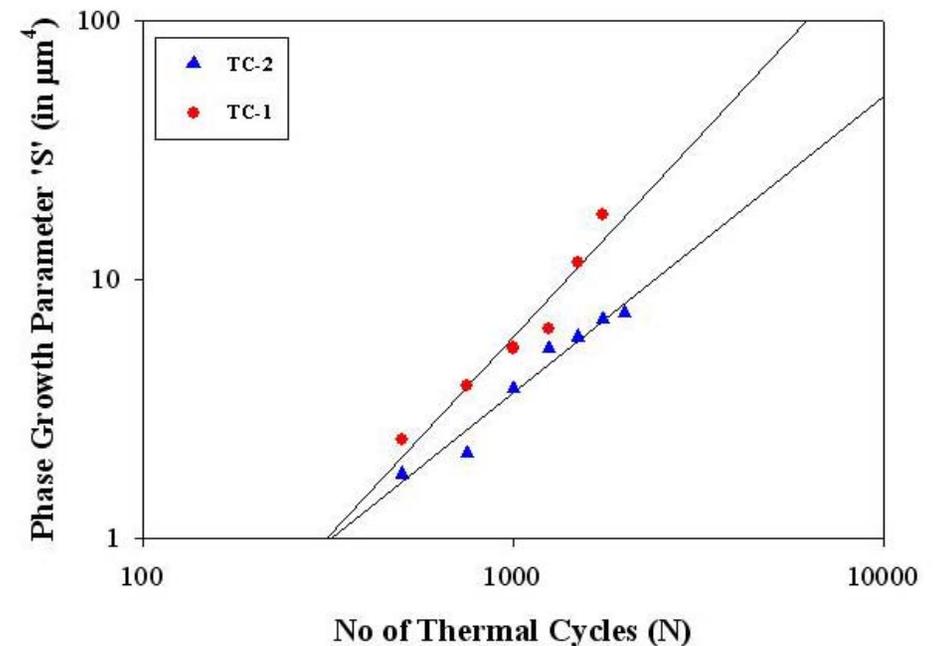


*SEM backscattered images, -55°C to 125°C, 96.5Sn3.0Ag0.5Cu solder, 256 I/O CABGA, magnification 750x*

Phase growth vs number of thermal cycles for 96.5Sn3.0Ag0.5Cu solder, **256 I/O PBGA**, subjected to

TC-1 (-55°C to 125°C)

TC-2 (0°C to 100°C)



# Case-1: Prior Damage in TC-1

Assembly has been *subjected to*  $N_A$  cycles in environment TC-1

Assembly is *withdrawn from service* and interrogated for damage state.

Prior *accrued damage* sustained by the system in TC-1 prognosticated.

$$S_A = g_A^4 - g_0^4 = a(N_A)^b$$

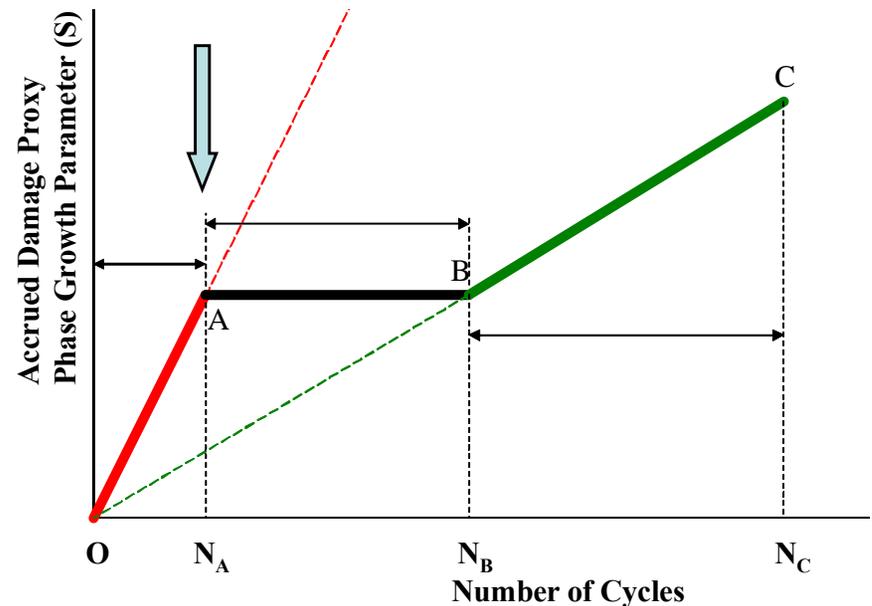
$$S_{A+\Delta N} = g_{A+\Delta N}^4 - g_0^4 = a(N_A + \Delta N)^b$$

$$S_{A+2\Delta N} = g_{A+2\Delta N}^4 - g_0^4 = a(N_A + 2\Delta N)^b$$

$$S_{A+3\Delta N} = g_{A+3\Delta N}^4 - g_0^4 = a(N_A + 3\Delta N)^b$$

*Subscript “p” appended at end of each prognosticated parameter.*

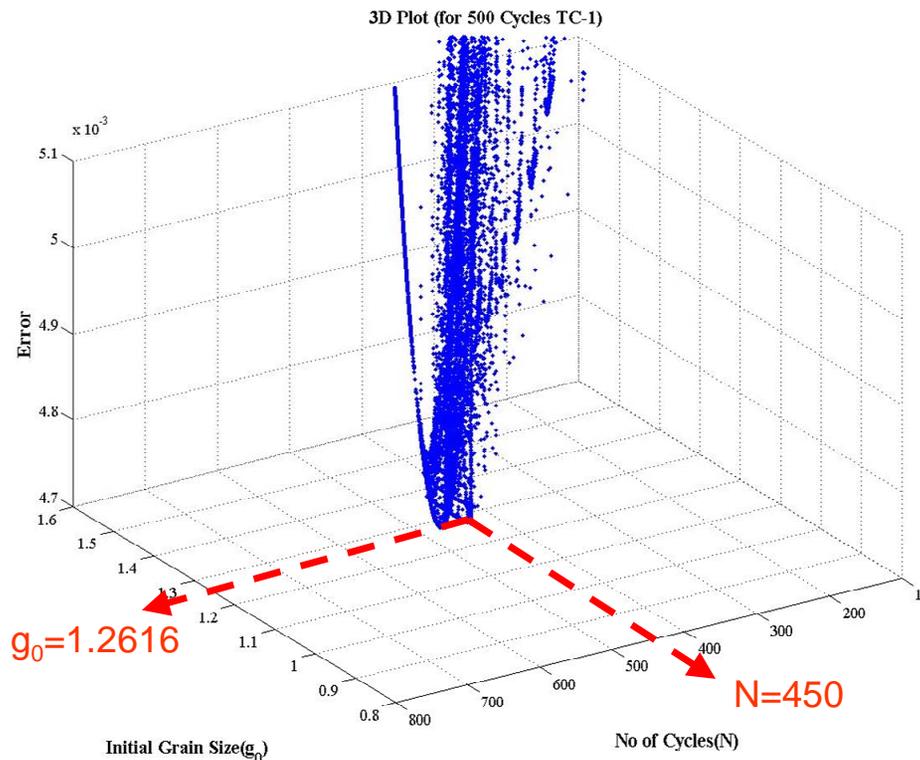
$$g_{0p}, a_p, b_p, N_{Ap}$$



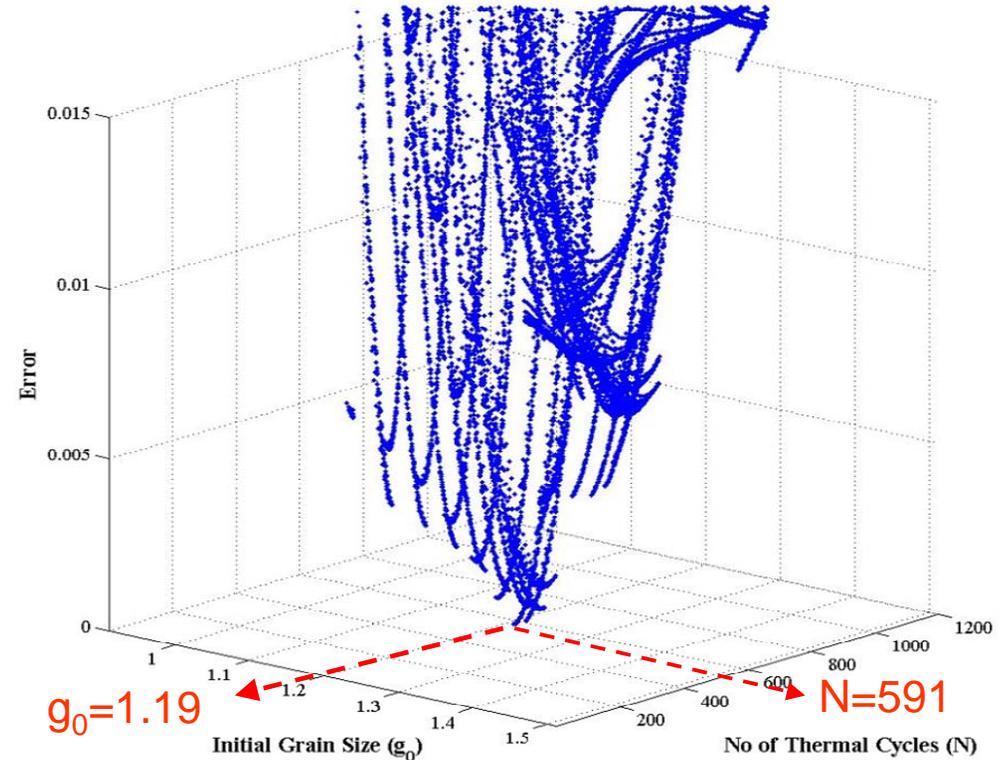
# Case-1: Prior Damage in TC-1

*Assembly subjected to known but undisclosed 500 cycles in environment TC-1*

Cycle Count	Cycle 'N'			Initial Grain Size 'g <sub>0</sub> ' (μm)		
	Expt Data	LM Alg	% Error	Expt Data	LM Alg	% Error
100 I/O CABGA	500	430	-14	1.258	1.076	-14.5
256 I/O BGA	500	591	18.2	1.065	1.262	18.5



*-55°C to 125°C, SAC305, 100 I/O CABGA*



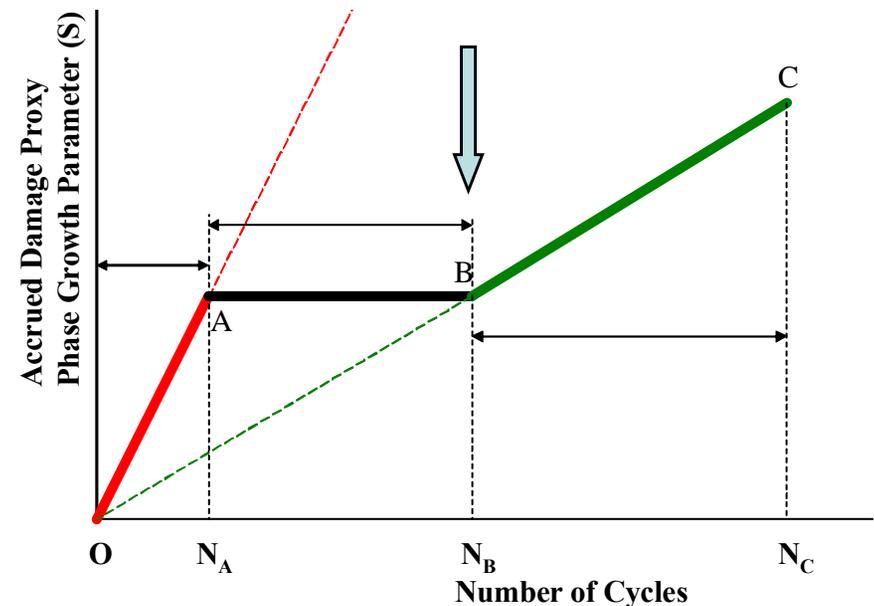
*-55°C to 125°C, SAC305, 256 I/O CABGA*

# Case-2: Operational Readiness in TC-2

Assess *operational readiness* of the electronic assembly in TC-2.

Prognostic sensor cells are subjected to a *small period* of exposure of TC-2.

Assembly prognosticated for *equivalent prior damage* TC-2

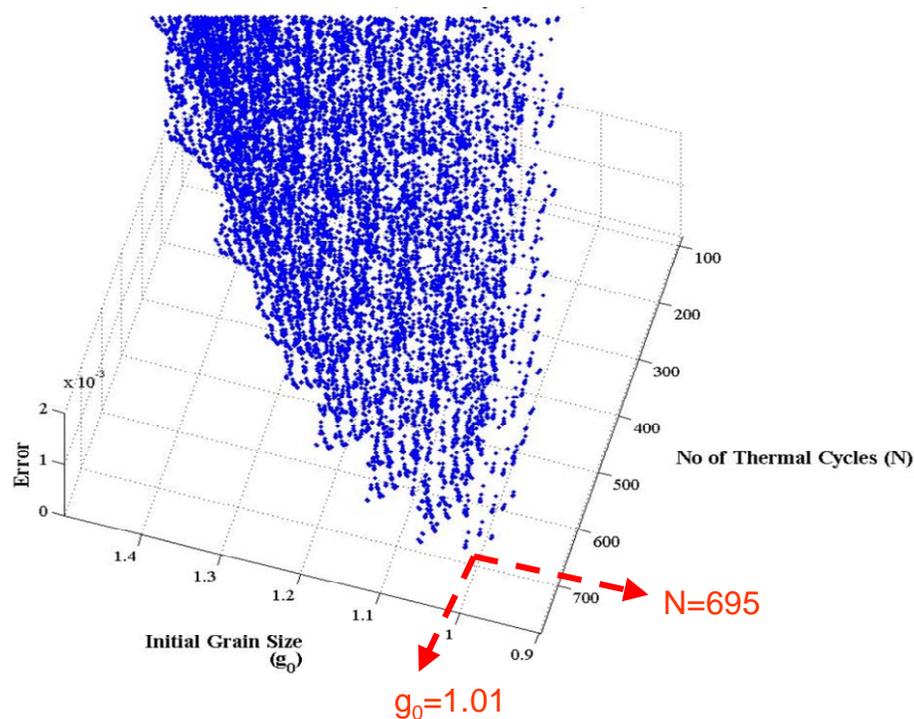


Cycles		100 I/O CABGA	256 I/O PBGA
a (TC-2)		6.90E-03	1.30E-03
b (TC-2)		0.9757	1.1462
$g_0$		1.258	1.065
$g_A = g_B$		1.591	1.386
Experimental Data	Cycles of TC-1	500	500
	Cycles of TC-2	662	708
	$\Delta D_e (N_B - N_A)$	162	208

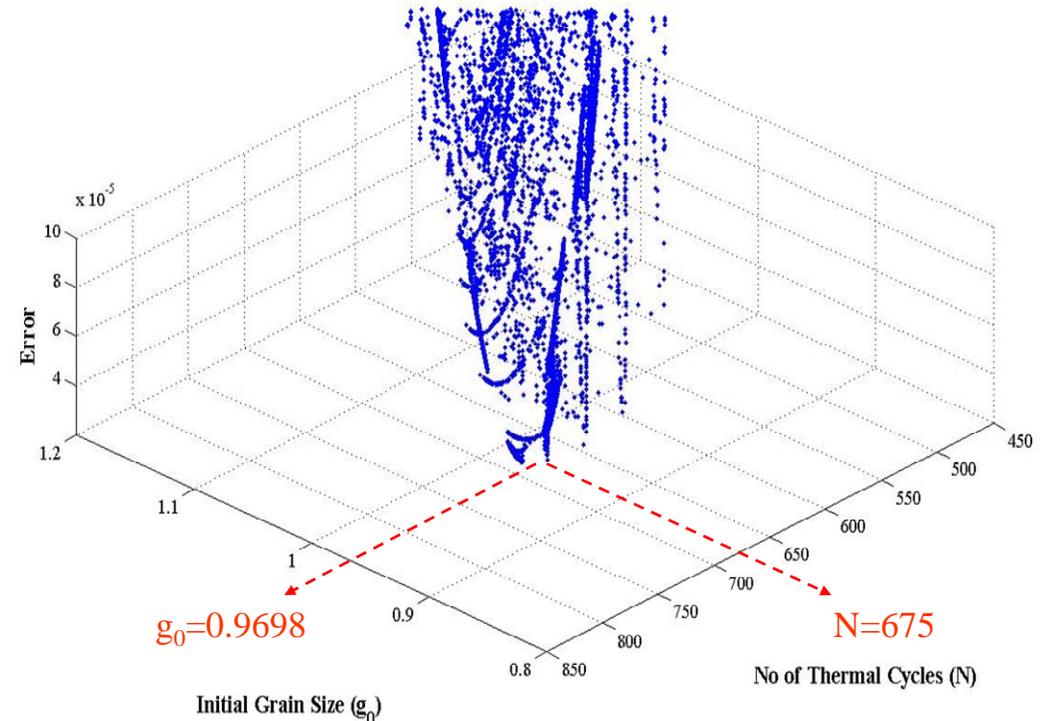
# Case-2: Operational Readiness in TC-2

A small subset of assemblies subjected to TC-2.

Samples from the condition monitoring cells exposed to a second environment TC-2 and withdrawn in 50 cycle increments



*-55°C to 125°C, SAC305, 100 I/O CABGA*



*-55°C to 125°C, SAC305, 256 I/O CABGA*

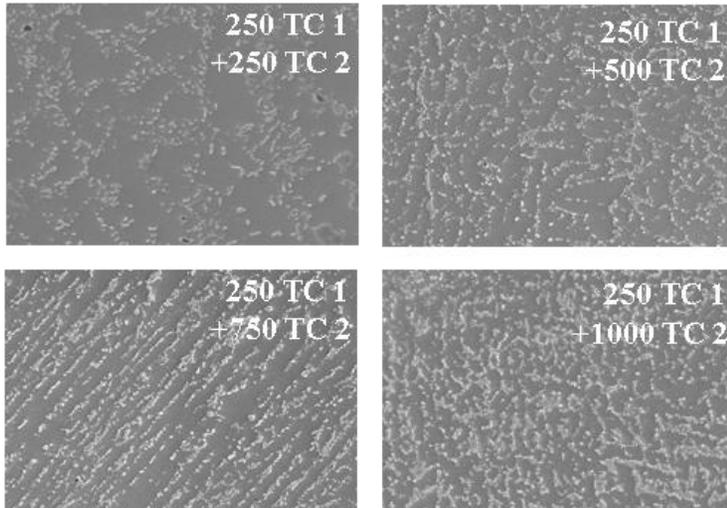
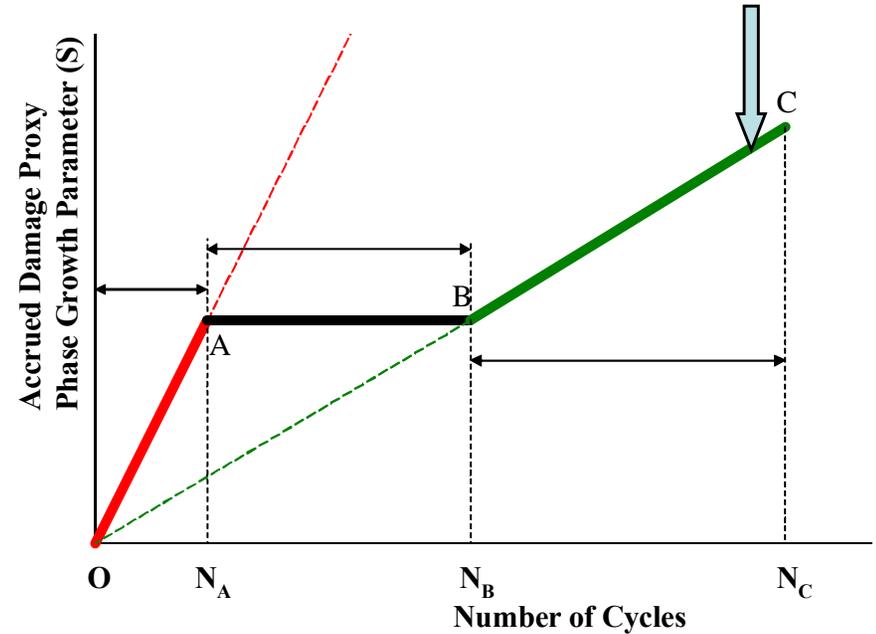
# Case-3: Residual Life in TC-2

Assembly was *deployed in TC-1*, and then *re-deployed in TC-2*.

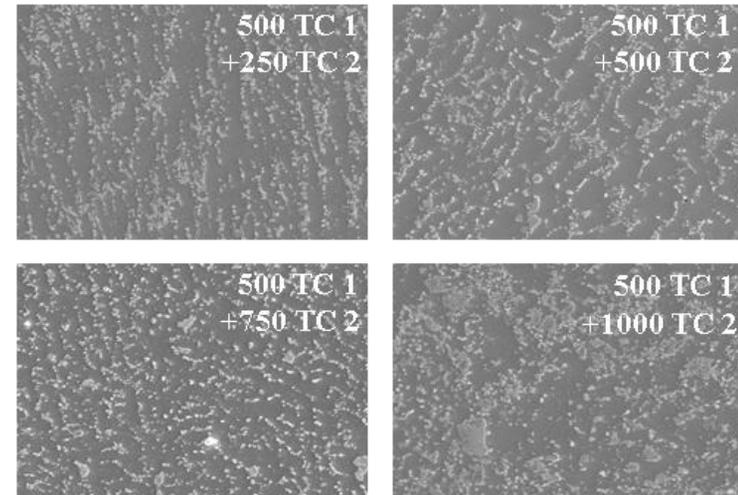
Assembly prognosticated for *prior damage* TC-1 and TC-2

Differential damage subtracted to account for the sequential thermal exposures.

$$N_C - N_B = N_{CP} - \Delta D - N_{AP}$$



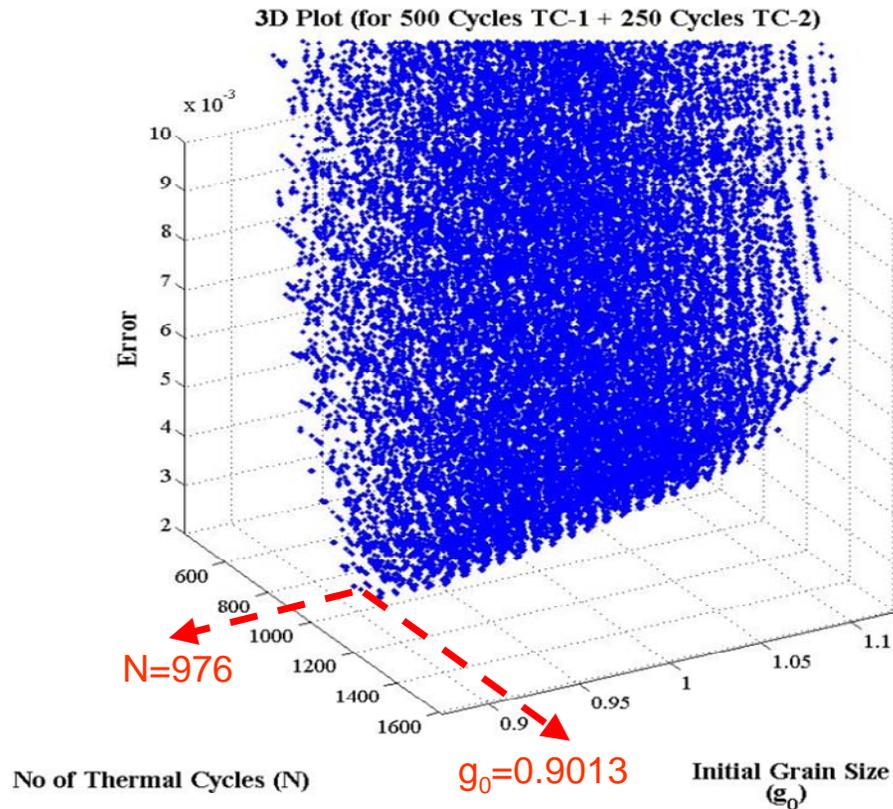
*250 Cycles of TC-1 + (x-cycles) of TC-2, SAC305, 256 PBGA, 750x*



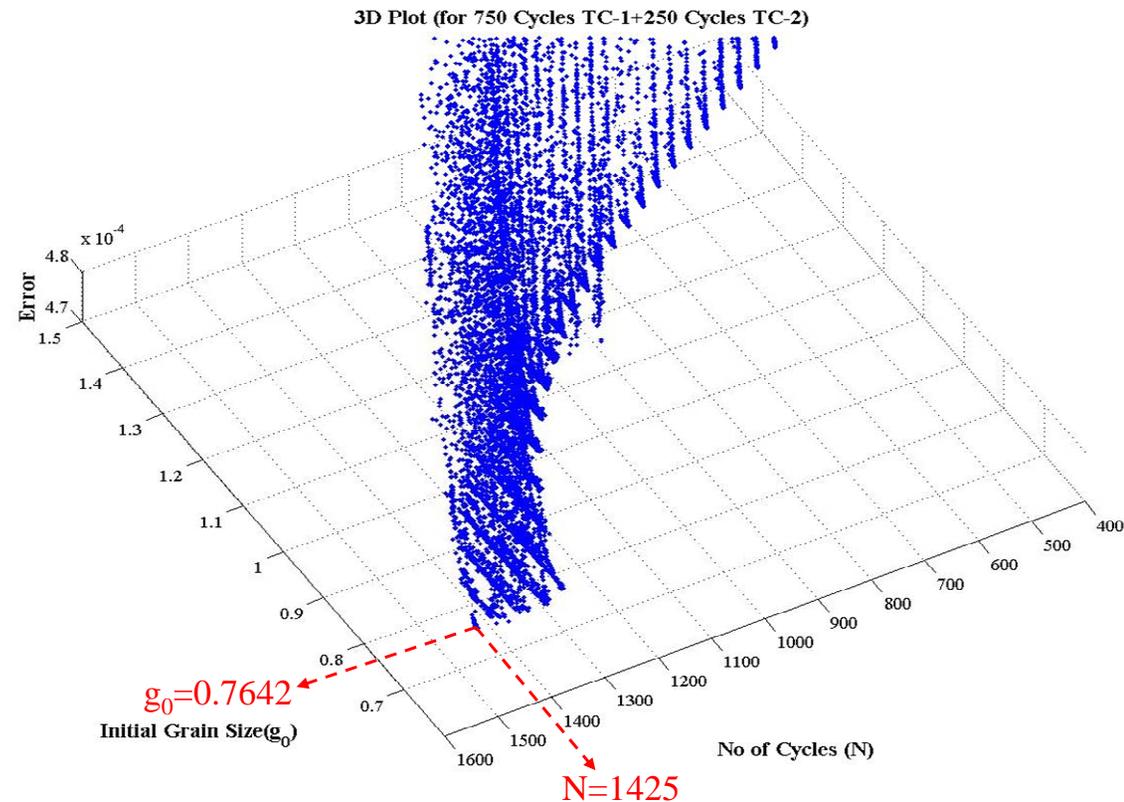
*500 Cycles of TC-1+( x-cycles) of TC-2, SAC305, 256 PBGA, 750x*

# Case-3: Residual Life in TC-2

Samples from the condition monitoring cells exposed to a second environment TC-2 and withdrawn in 50 cycle increments

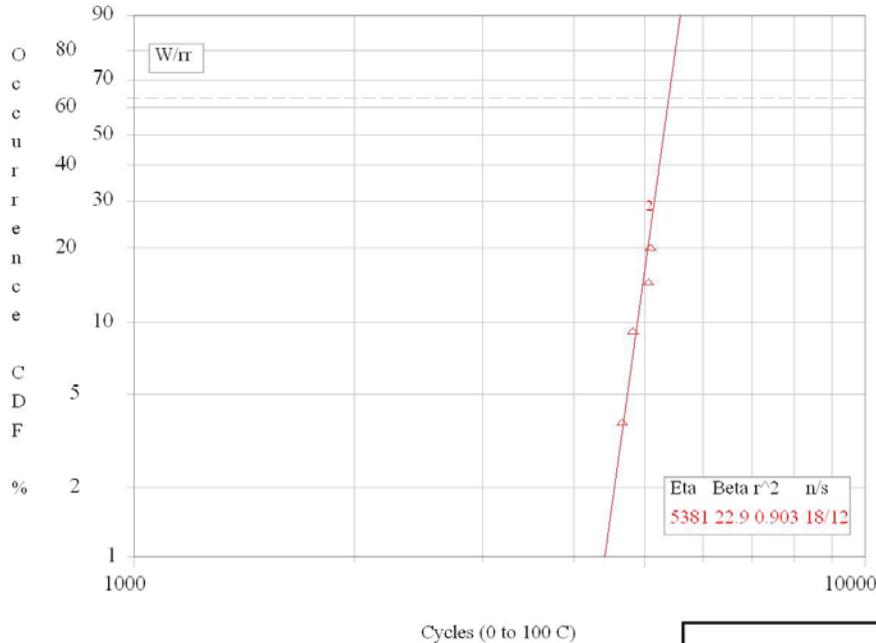


256 PBGA 96.5Sn3.0Ag0.5Cu Solder subjected to 500 Cycles TC-1 + 250 Cycles TC-2.



256 PBGA 96.5Sn3.0Ag0.5Cu Solder subjected to 750 Cycles TC-1 + 250 Cycles TC-2.

# Case-3: Residual Life in TC-2



Cycle count	Prognosticated Cycles	$N_{1\%}$	RL
Damage in TC-2	695	4866	4171

*Calculation of  $N_{1\%}$  from Weibull plot of failure data.*

	Cycle Count	$N_{Cp}$	$\Delta D_p$ ( $N_{Bp} - N_{Ap}$ )	$N_{Ap}$	Experiment $N_C - N_B$	Prognostication $N_{Cp} - N_{Bp}$ $= N_{Cp} - \Delta D_p - N_{Ap}$
256 I/O BGA	500 TC1 +250 TC2	976	175	430	250	371
256 I/O BGA	750 TC1 + 250 TC2	1425	495	710	250	220

# Part-I: Summary and Conclusions

---



PHM approach has been developed for interrogation of damage state of electronics subjected to multiple thermal environments.

Approach is based on leading indicators of failure derived from micro-structural evolution of damage in second-level interconnects.

Case studies have been presented to demonstrate the ability of the approach for assessment of accrued damage and the residual life after exposure to multiple environments.

Prognosticated latent damage correlates with experimental results for leadfree alloys in area-array packaging.

Correlation demonstrates that the presented leading indicators based PHM technique can be used to interrogate the system state in multiple environments.

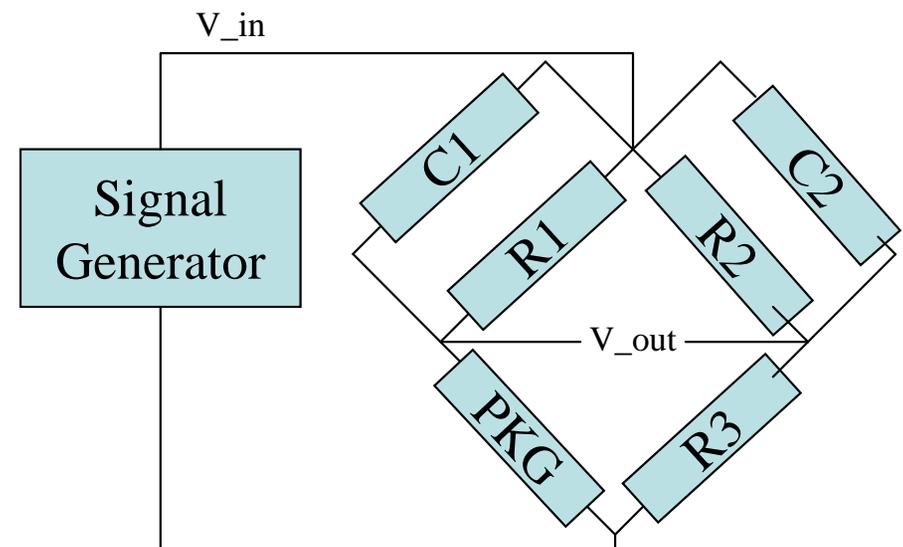
# Approach: Shock & Vibration

Interconnect resistance characteristics have been used to determine leading indicators of failure

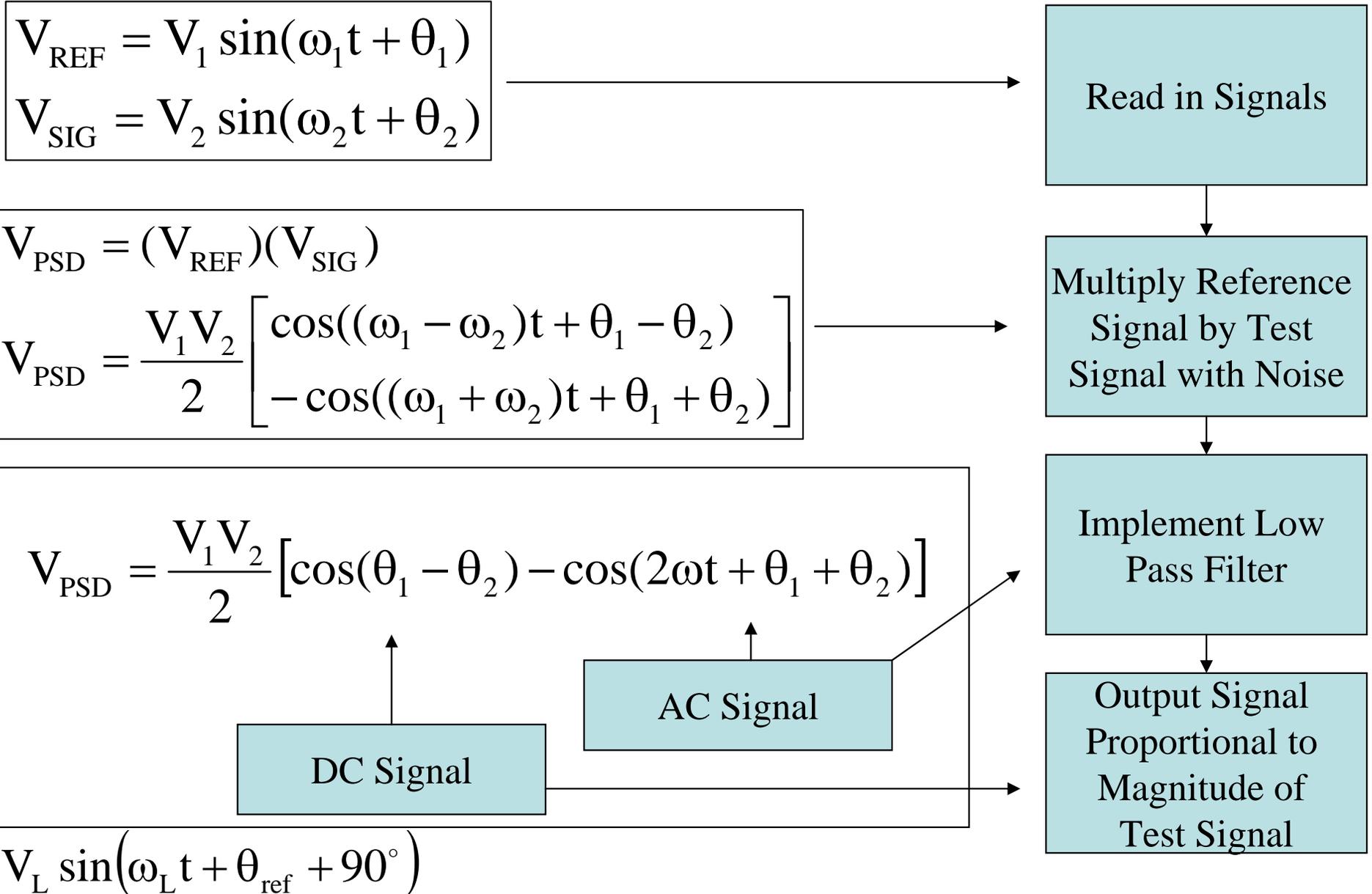
Phase shift of resistance spectroscopy output signal is used instead of magnitude

Drop and vibration environments have been investigated

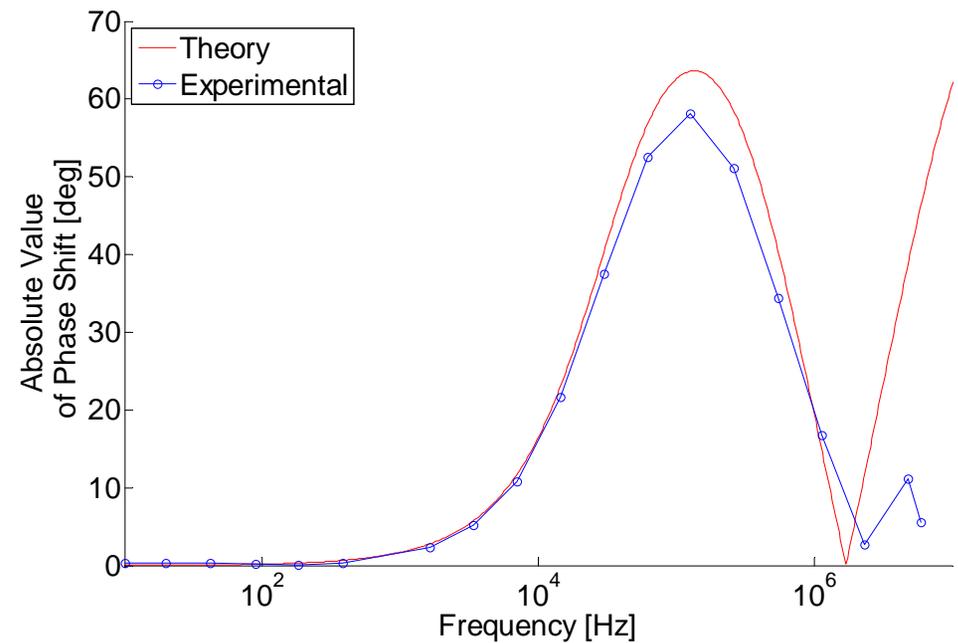
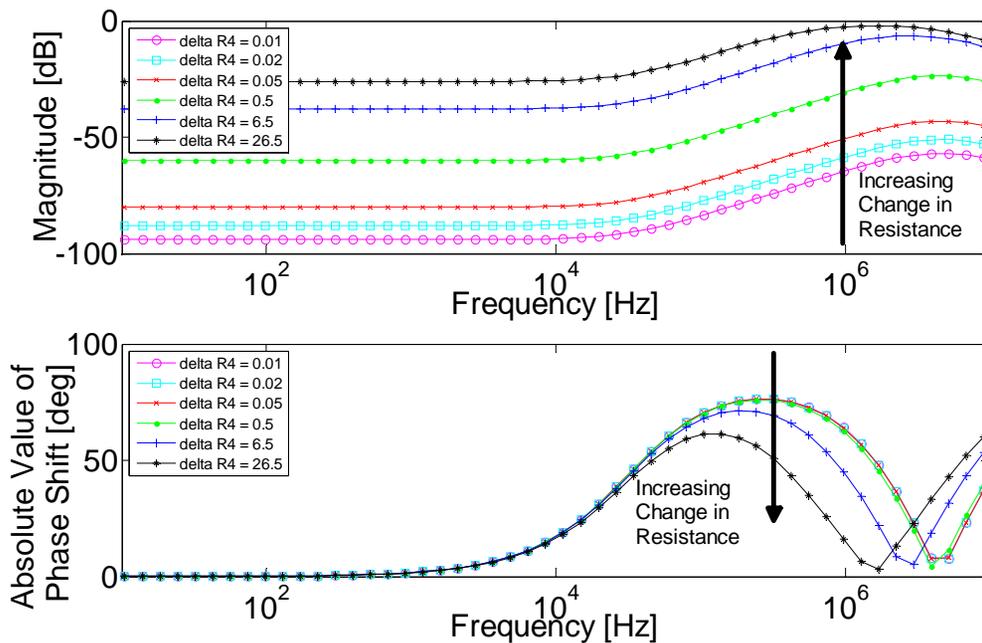
Data is collected on BGA components at varying frequencies



# Phase Sensitive Detection



# Theoretical vs Experimental



*Bode Plots of Theoretical Transfer function. Arrows indicate trends of increasing resistance of the package*

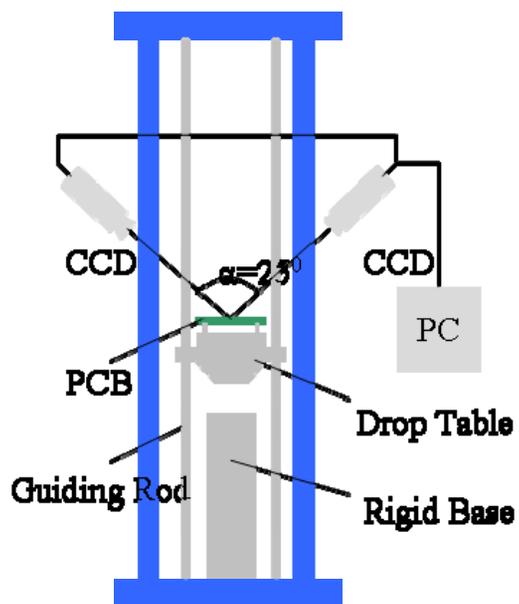
# Test Setup

## - Shock and Vibration

1500G's, 0.5 ms

Packages face down

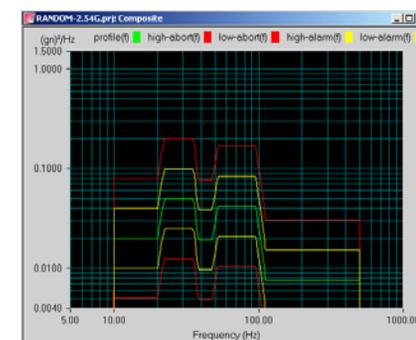
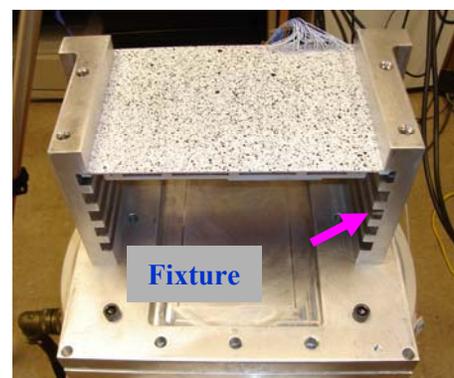
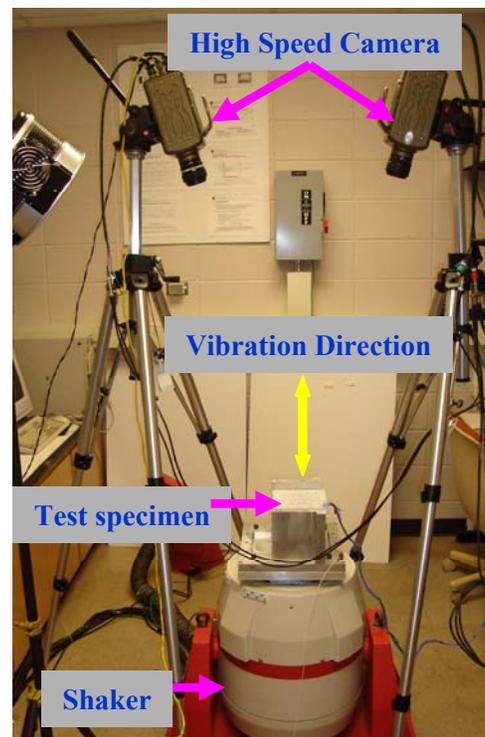
10M Samples/second



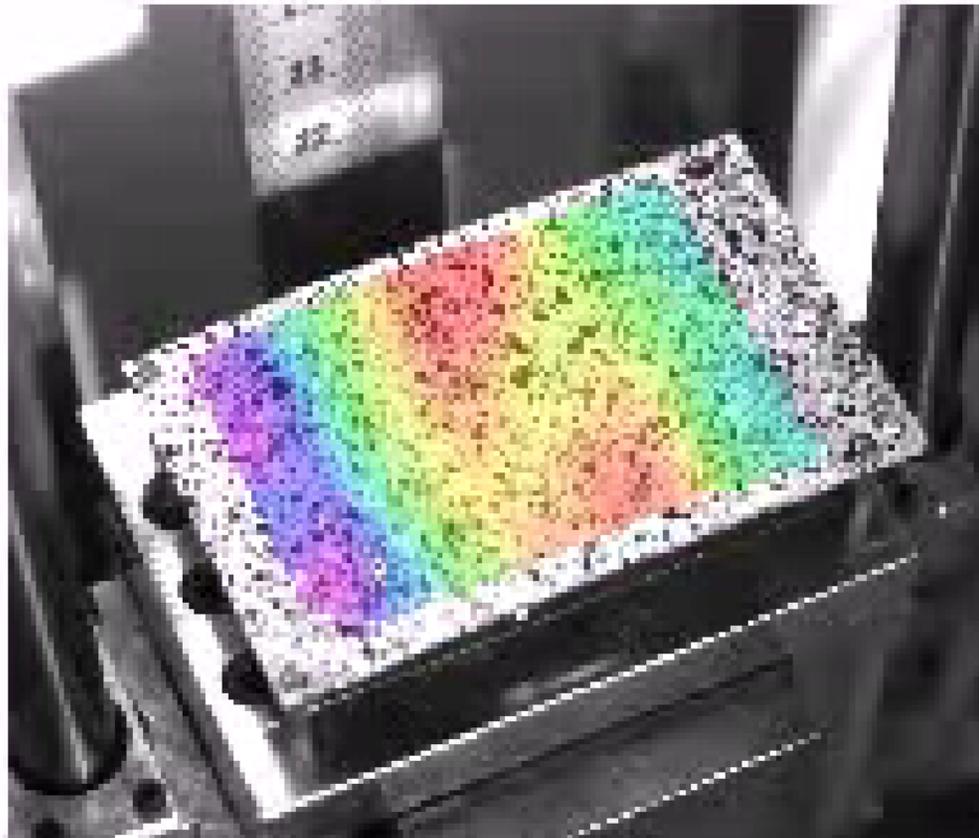
*Drop tower and high speed digital cameras for digital image correlation*



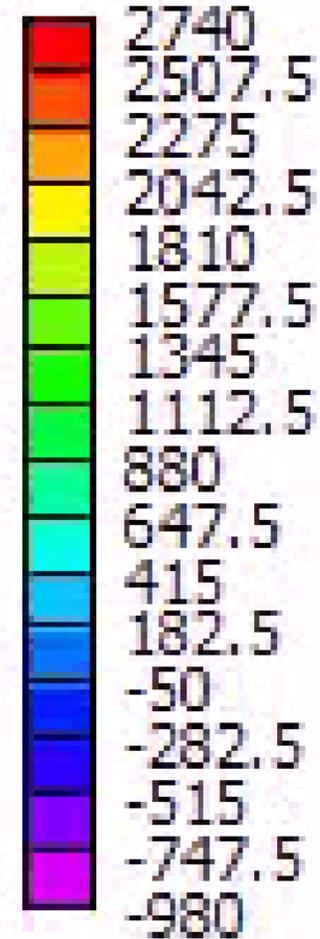
*Lansmont Model 23 Shock Test System*



Random Profile from  
12-500 Hz at 2.54 Grms

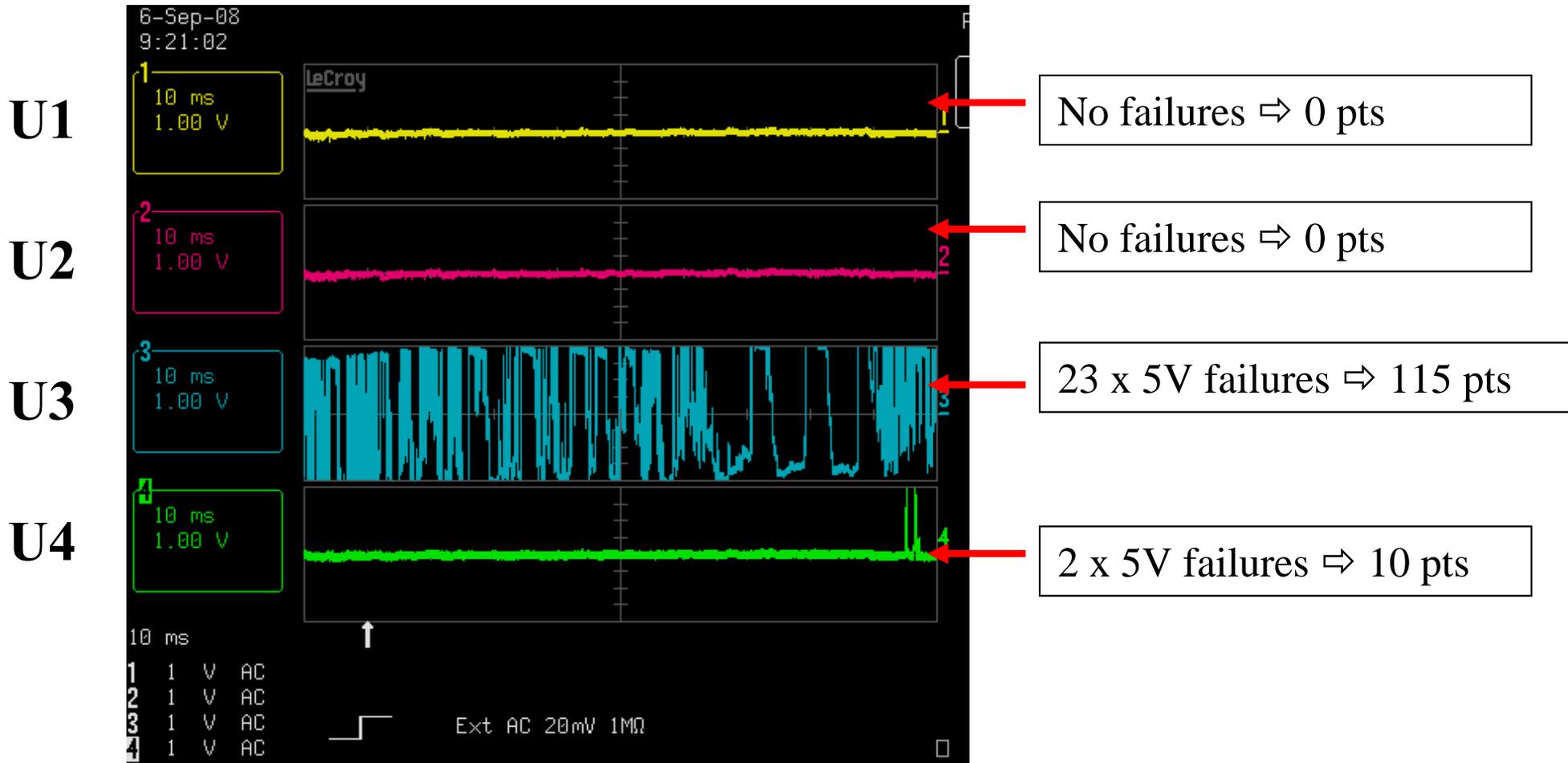


exx [ $\mu\text{m}/\text{m}$ ] - Lagrange



# Definition of Failure

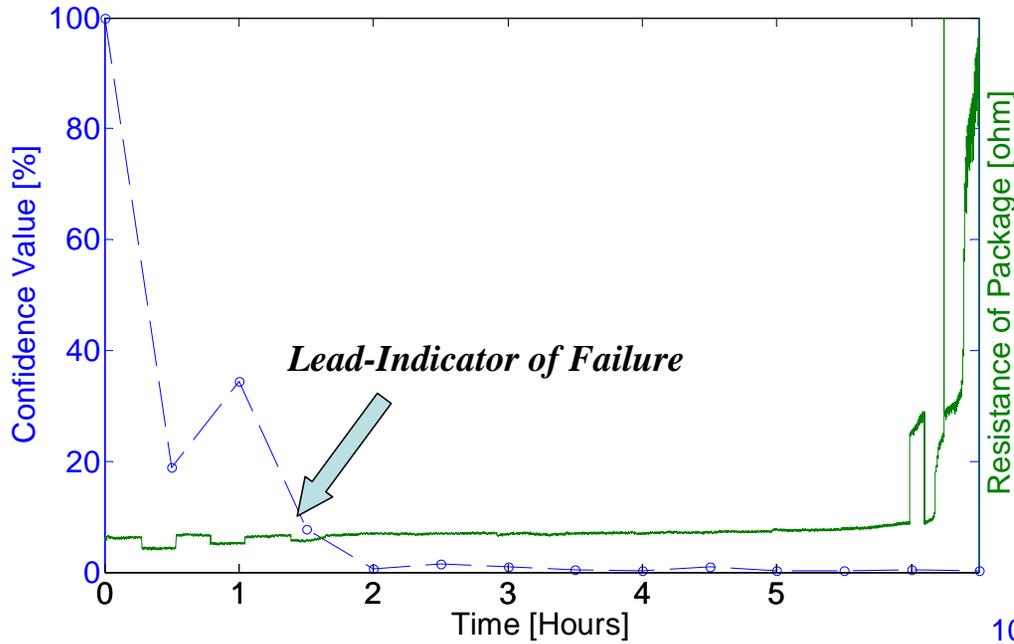
- *Electrical Continuity x Peak Magnitude*



*Electrical Continuity Output from DSO, and failure metric calculation*

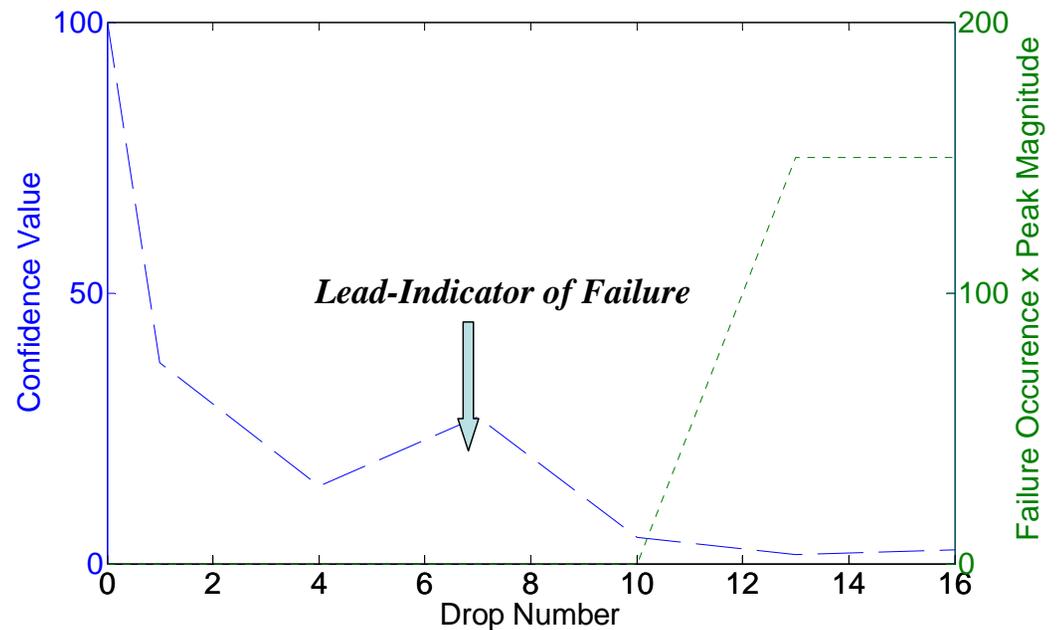
# Statistical Assessment of Damage

## - Vibration, CV vs. Time (127 KHz)



*Phase shift as a lead indicator of failure  
(Test Board-B, PBGA676, 127kHz)*

*Confidence value as a lead indicator of failure during a drop test  
(Test Board-B, PBGA676)*

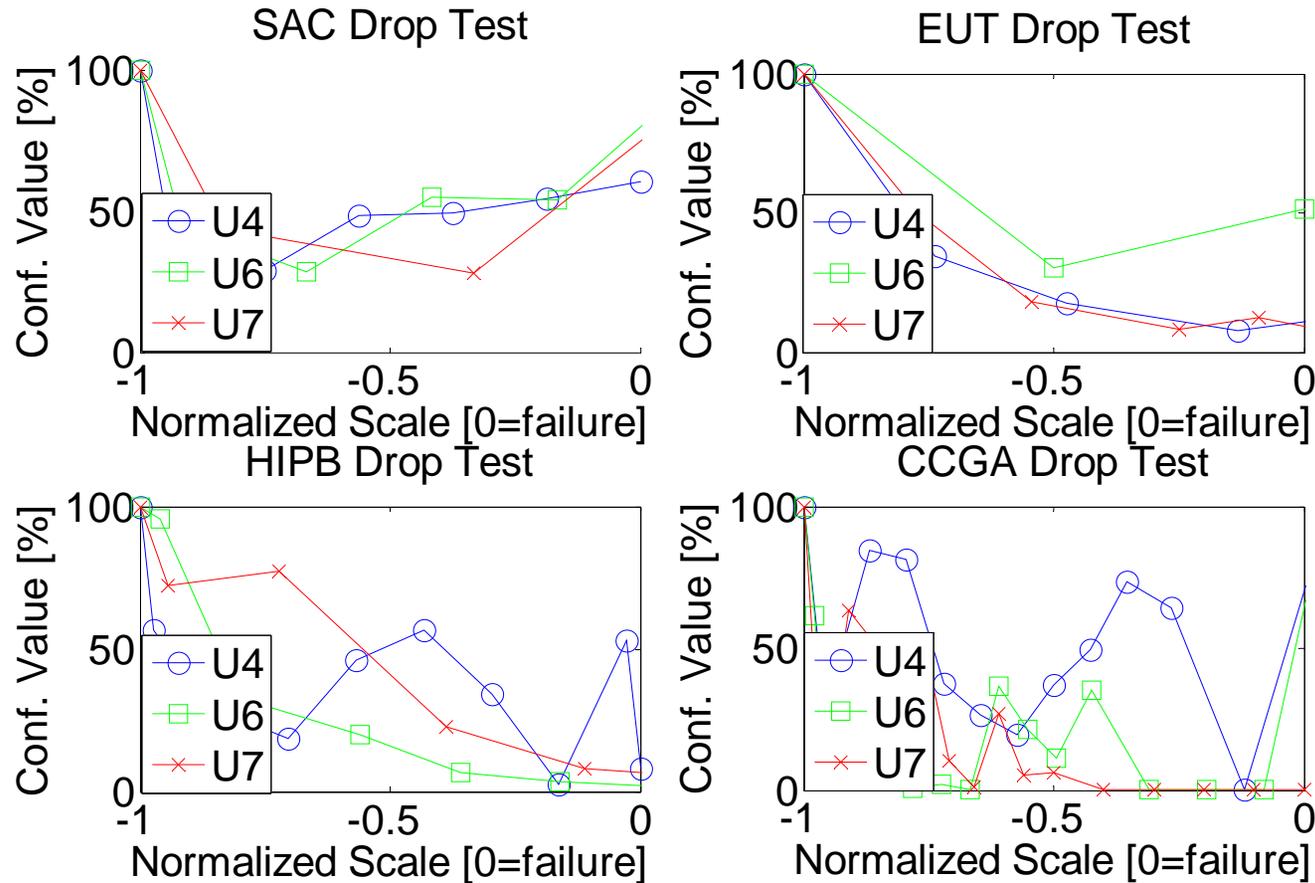


# Effect of Interconnect Architecture



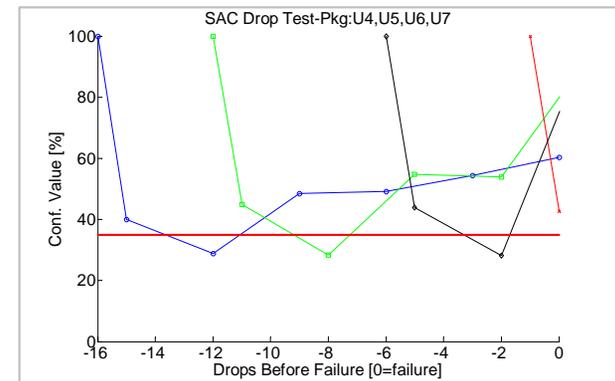
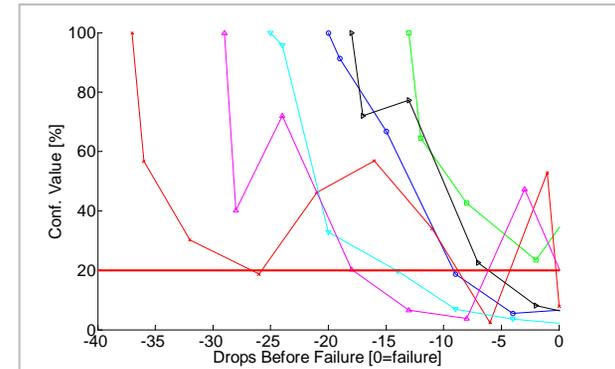
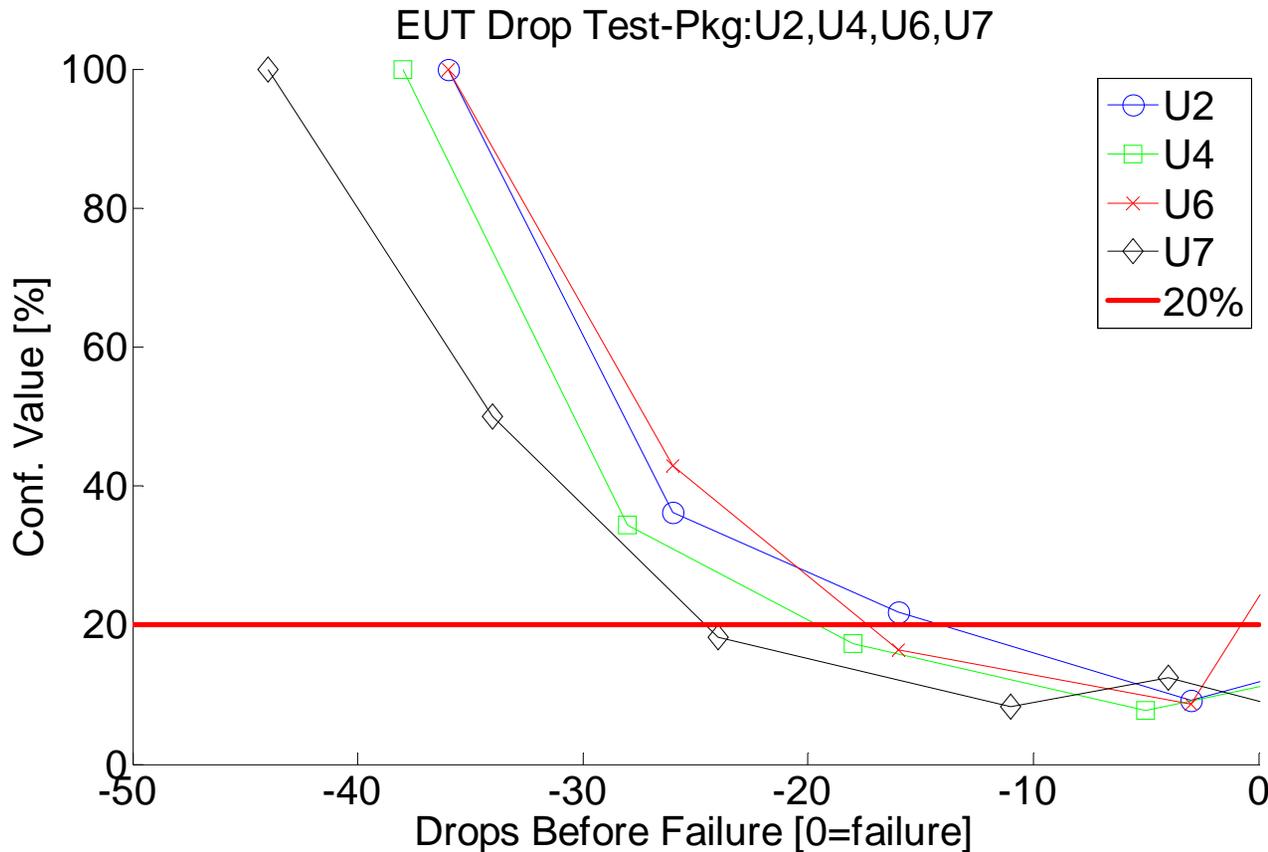
cave<sup>3</sup>  
Research  
Center

- All Interconnects (Package U4, 6MHz)



*Degradation of confidence value during drop test of packages U4, U6 and U7 on a normalized scale for all interconnects. U4 is shown with blue circles, U5 is shown with green squares and U6 is shown with red crosses (Test Board-A, 6MHz)*

# Threshold for Prognostic Distance



*Method for determining prognostic distance using a threshold value shown in red. Each trace is a individual package. (Test Board-A)*

# Prognostic Distance

> *CV vs Time (2.33MHz, 6 MHz)*

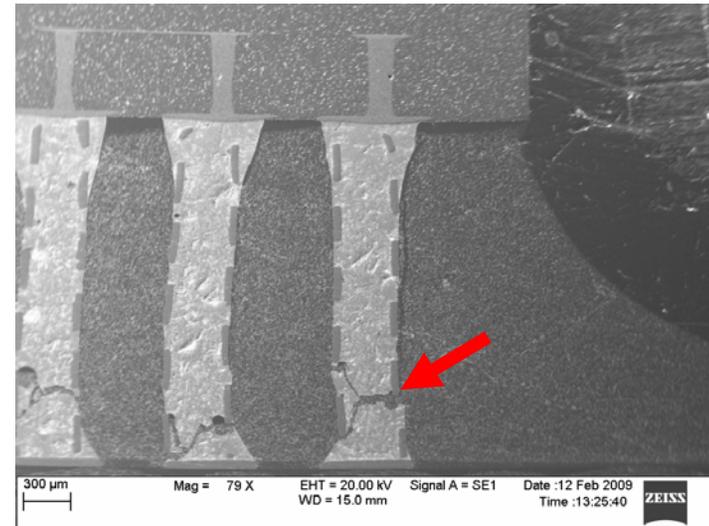
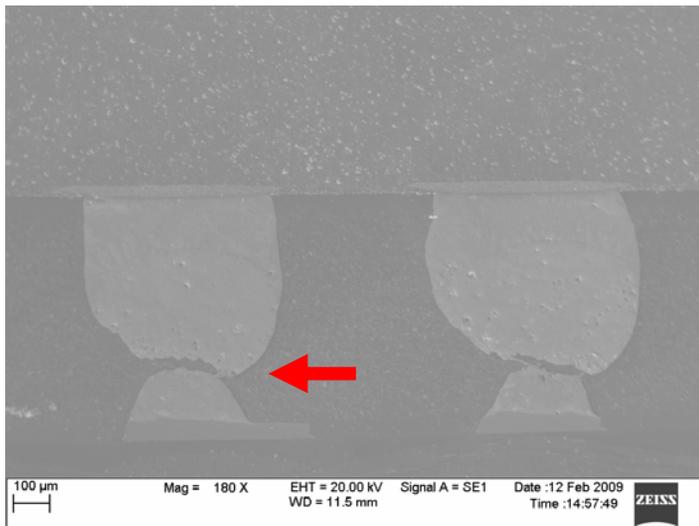
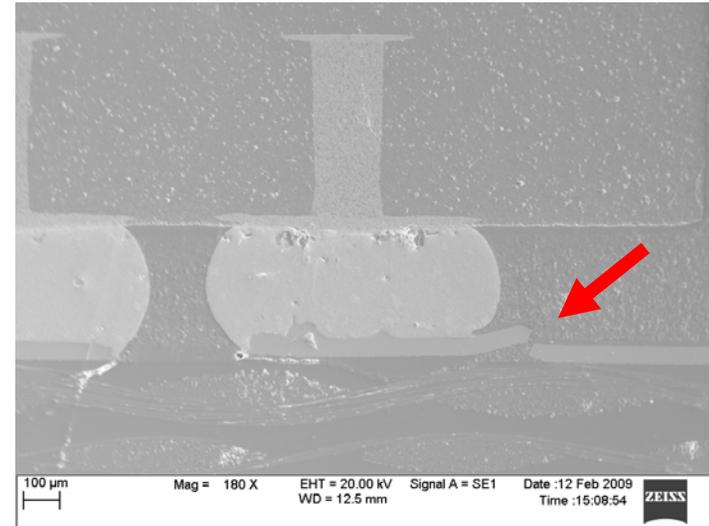
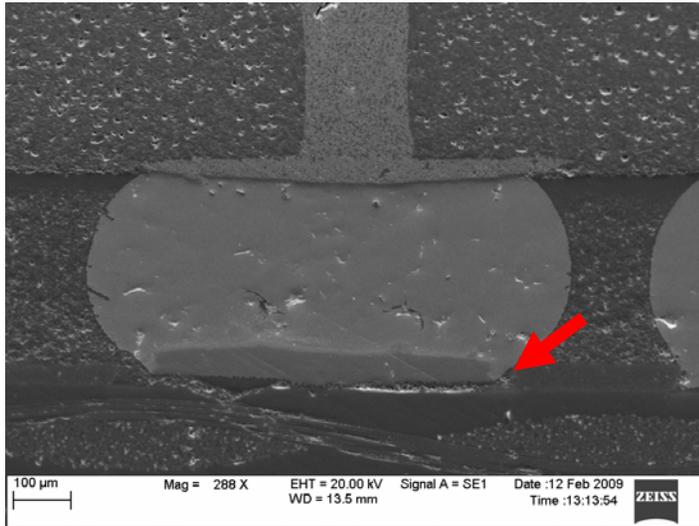


**cave<sup>3</sup>**  
Research  
Center

Interconnect Type	Frequency	Threshold Confidence Value (%)	Average Prognostic Distance (No of Drops)	Std. Deviation (No of Drops)	False Positives
SAC305	2.33MHz	50	8.33	5.03	0
63Sn37Pb	2.33MHz	70	23.75	13.43	0
90Pb10Sn	2.33MHz	85	18.17	10.65	0
Cu-CCGA	2.33MHz	30	22.75	10.9	0

Interconnect Type	Frequency	Threshold Confidence Value (%)	Average Prognostic Distance (No of Drops)	Std. Deviation (No of Drops)	False Positives
SAC305	6 MHz	35	9	4	0
63Sn37Pb	6 MHz	20	18.75	4.65	0
90Pb10Sn	6 MHz	25	13.17	9.85	0
Cu-CCGA	6 MHz	30	43.5	23.39	0

# Failure Modes



# Part-II: Summary and Conclusions

---



A technique based on resistance measurements of solder interconnects has been developed to derive damage pre-cursors for electronic assemblies

Measurements of prognostic distance exhibit that the presented techniques can be used for early detection of impending failure in electronics

Prognostic distances have been quantified for various interconnects, and all have been shown to be positive

The trade off between prognostic distance and the propensity of a false positive have been shown to be inversely proportionate using this technique